

FDPF2710T

250V N-Channel PowerTrench MOSFET

General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

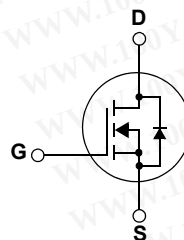
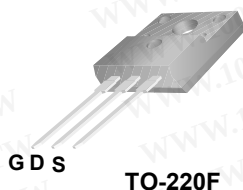
Application

- Ballast Application



Description

- 25A, 250V, $R_{DS(on)} = 36.3m\Omega$ @ $V_{GS} = 10V$
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low $R_{DS(on)}$
- High power and current handling capability



Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{DS}	Drain-Source Voltage	250	V
V_{GS}	Gate-Source voltage	± 30	V
I_D	Drain Current - Continuous ($T_C = 25^\circ C$) - Continuous ($T_C = 100^\circ C$)	25 18.8	A A
I_{DM}	Drain Current - Pulsed (Note 1)	100	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	145	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ C$) - Derate above $25^\circ C$	62.5 0.5	W W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Min	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	2.0	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ C/W$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDPF2710T	FDPF2710T	TO-220F	--	--	50

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA, T _J = 25°C	250	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	--	0.25	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 250V, V _{GS} = 0V V _{DS} = 250V, V _{GS} = 0V, T _C = 125°C	-- --	-- --	10 500	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3.0	3.9	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 25A	--	36.3	42.5	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 10V, I _D = 25A (Note 4)	--	63	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	--	5470	7280	pF
C _{oss}	Output Capacitance		--	426	567	pF
C _{rss}	Reverse Transfer Capacitance		--	97	146	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 125V, I _D = 50A V _{GS} = 10V, R _{GEN} = 25Ω (Note 4, 5)	--	80	170	ns
t _r	Turn-On Rise Time		--	252	514	ns
t _{d(off)}	Turn-Off Delay Time		--	112	234	ns
t _f	Turn-Off Fall Time		--	154	318	ns
Q _g	Total Gate Charge	V _{DS} = 125V, I _D = 50A V _{GS} = 10V (Note 4, 5)	--	78	101	nC
Q _{gs}	Gate-Source Charge		--	34	--	nC
Q _{gd}	Gate-Drain Charge		--	18	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	25	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	150	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 25A	--	--	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 50A dI _F /dt = 130A/μs (Note 4)	--	163	--	ns
Q _{rr}	Reverse Recovery Charge		--	1.3	--	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 1\text{mH}$, $I_{AS} = 17A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 50A$, $dI/dt \leq 200A/\mu s$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

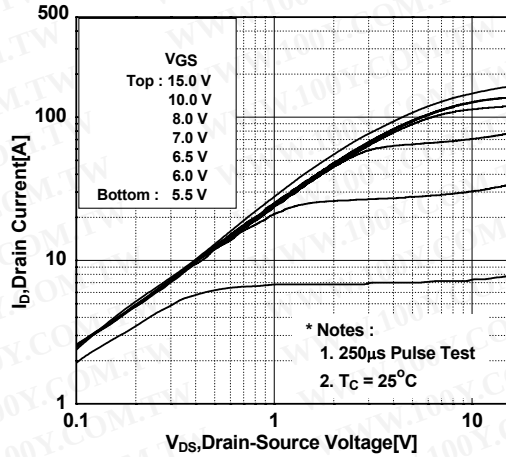


Figure 2. Transfer Characteristics

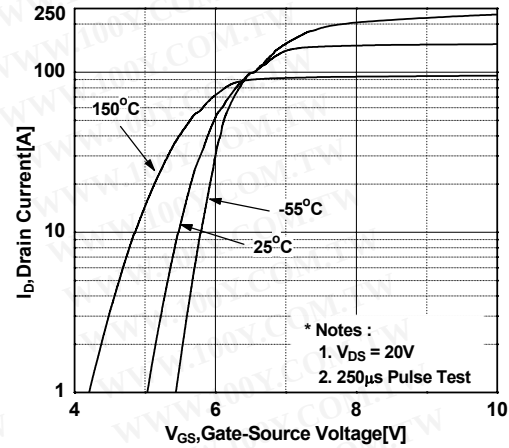


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

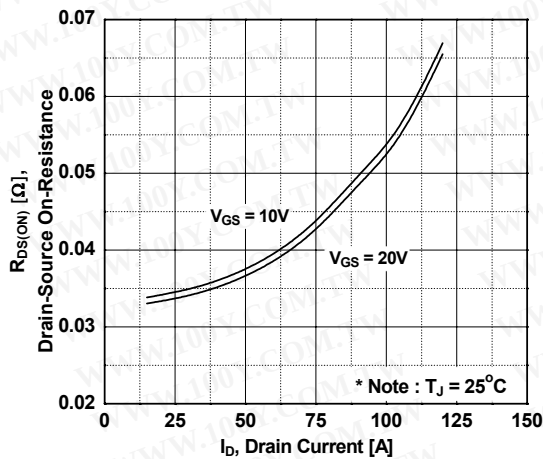


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

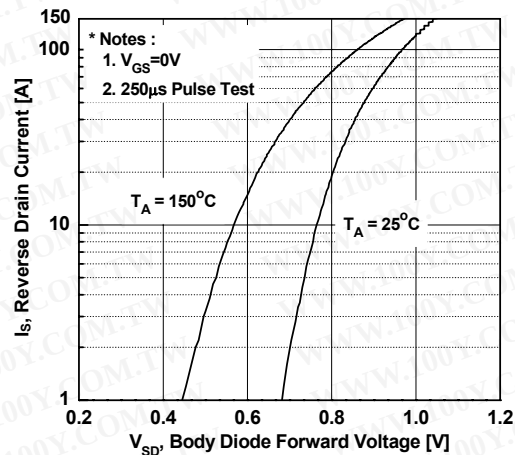


Figure 5. Capacitance Characteristics

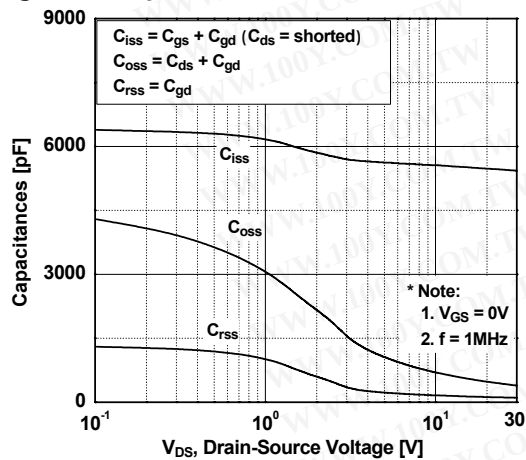
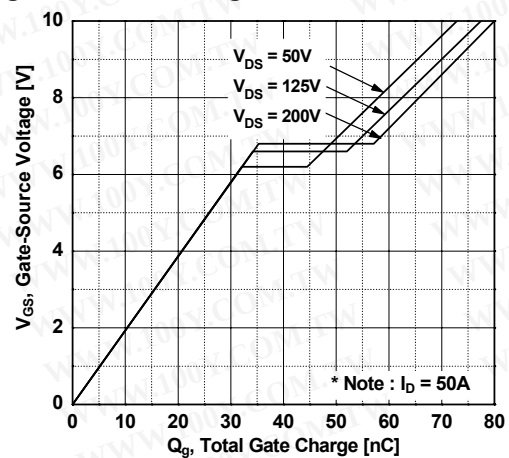


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

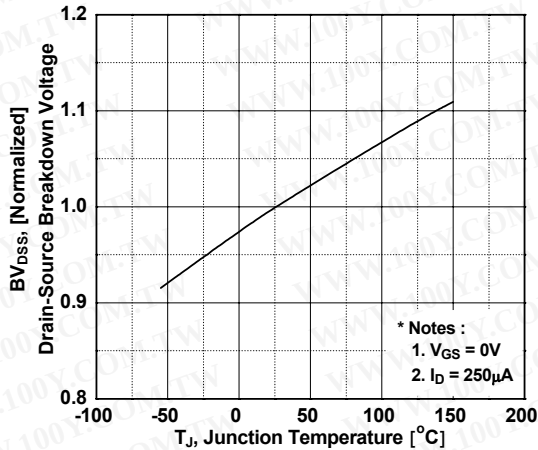


Figure 8. On-Resistance Variation vs. Temperature

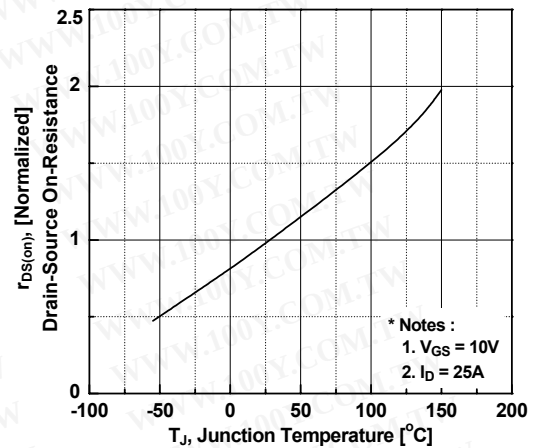


Figure 9. Maximum Safe Operating Area

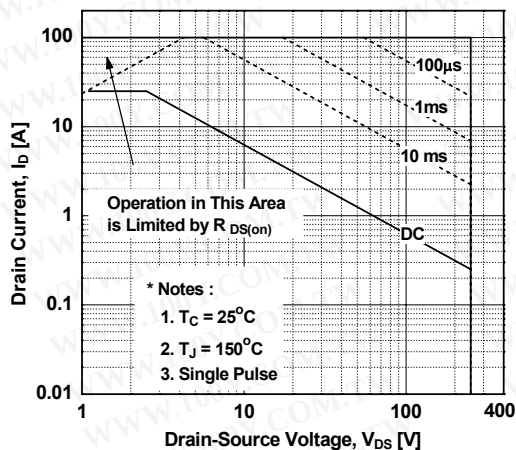


Figure 10. Maximum Drain Current vs. Case Temperature

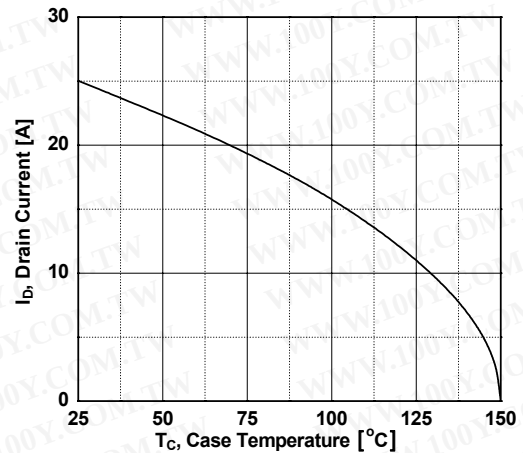
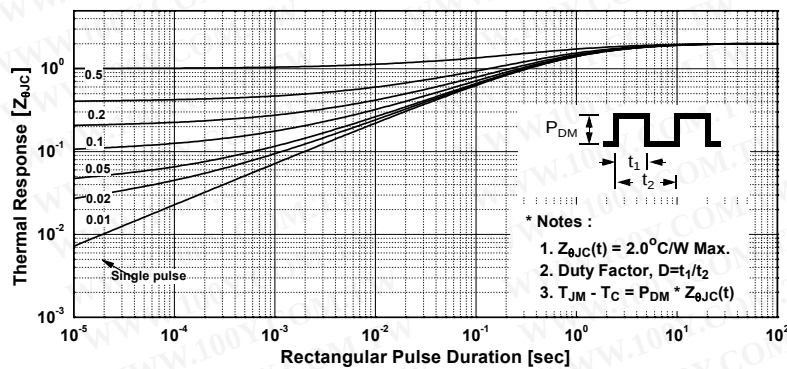
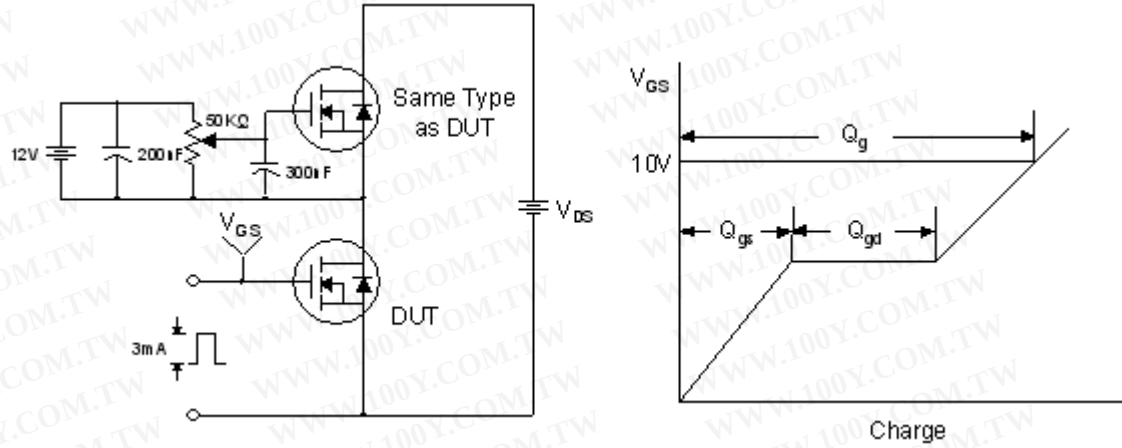


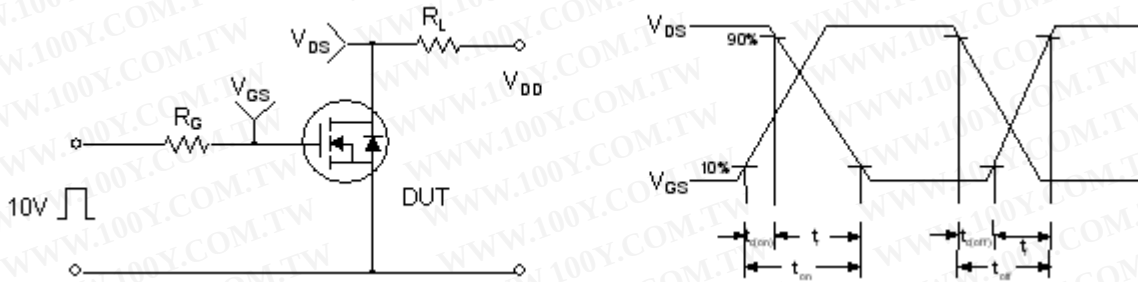
Figure 11. Transient Thermal Response Curve



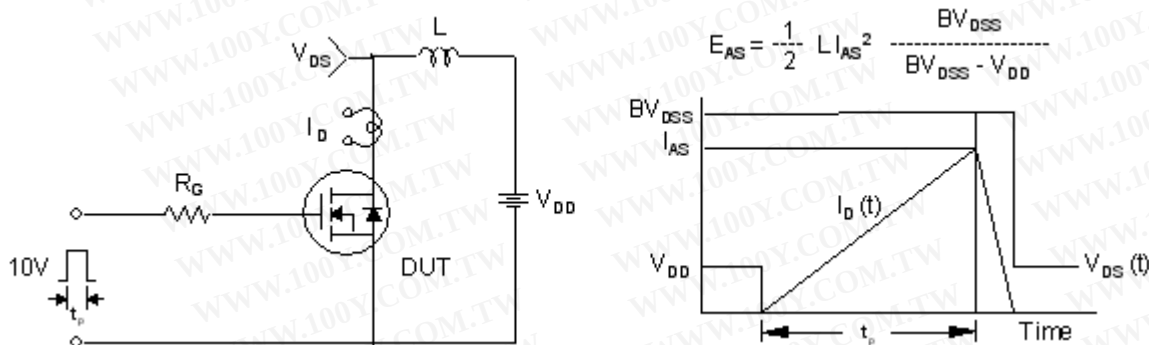
Gate Charge Test Circuit & Waveform



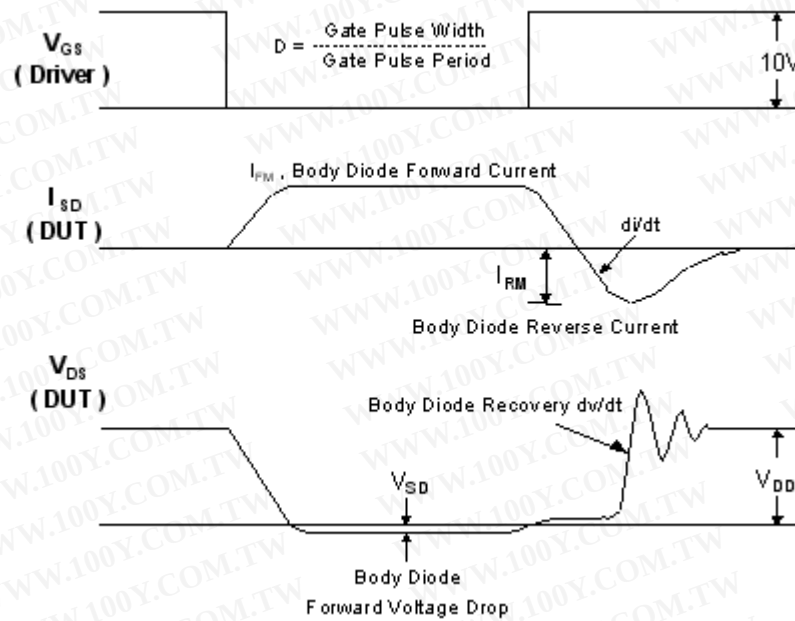
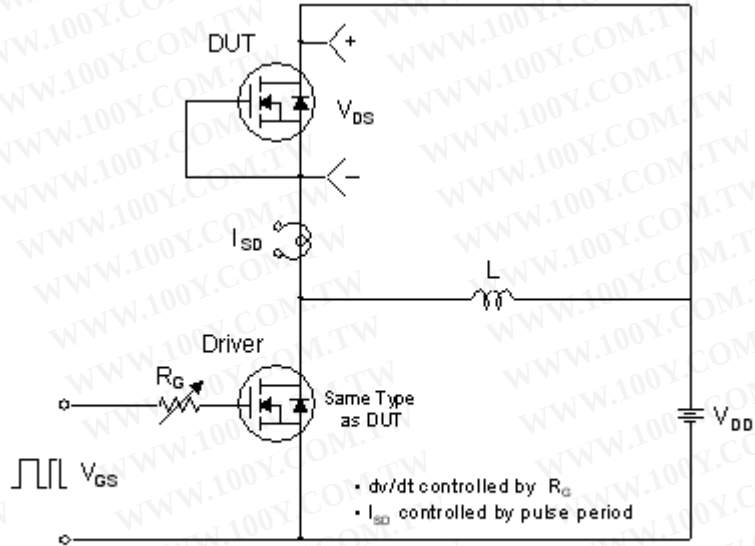
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms





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